1. General description

NPN/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

· General-purpose switching and amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	45	V	
I _C	collector current			-	-	100	mA	
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$		200	-	450		



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1	6 5 4	
3	C2	collector TR2		(TR1)
4	E2	emitter TR2		
5	B2	base TR2	∐1 ∐2 ∐3	
6	C1	collector TR1	TSSOP6 (SOT363)	sym139

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BC847BPN-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC847BPN-Q	13%

[1] % = placeholder for manufacturing site code

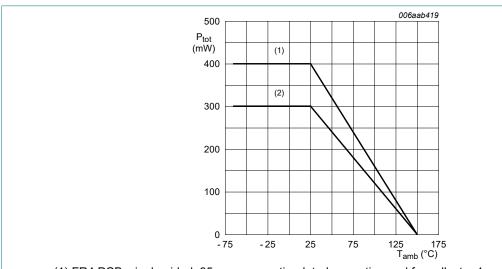
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor wit	h negative polarity	-	<u> </u>		
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	200	mA
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	220	mW
			[2]	-	250	mW
Per device	<u> </u>		'	1		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	400	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm²
- (2) FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

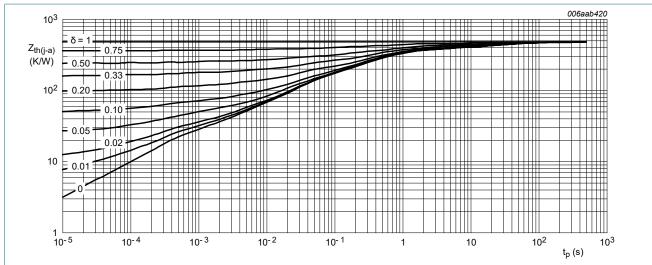
Fig. 1. Per device: Power derating curves SOT363 (SC-88)

9. Thermal characteristics

Table 6. Thermal characteristics

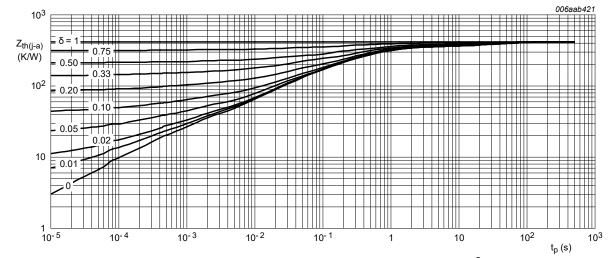
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor		,				
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air [1]	[1]	-	-	568	K/W
		[2]	-	-	500	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	230	K/W
Per device	,		,				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W
• ,			[2]	-	-	313	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm²

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

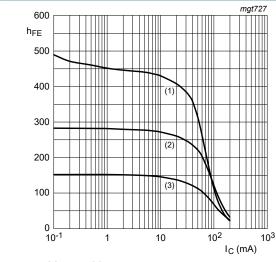
BC847BPN-Q

10. Characteristics

Table 7. Characteristics

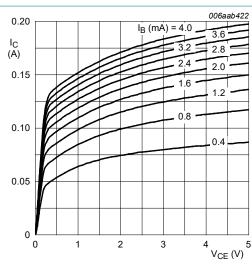
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or; for the PNP transistor v	with negative polarity				
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	45	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	15	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	200	-	450	
V _{CEsat}	collector-emitter	I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	-	100	mV
saturation voltage	saturation voltage	I_C = 100 mA; I_B = 5 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	300	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	755	-	mV
V_{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	580	655	700	mV
			600	655	750	mV
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz;	-	-	1.5	pF
		T _{amb} = 25 °C	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$	-	11	-	pF
		f = 1 MHz; T _{amb} = 25 °C	-	10	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	100	-	-	MHz

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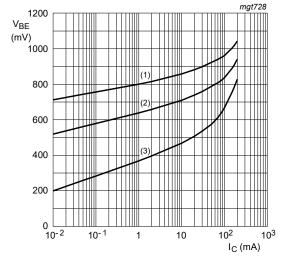
V_{CE} = 5 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

NPN transistor: DC current gain as a function of Fig. 4. collector current; typical values



 T_{amb} = 25 °C

Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



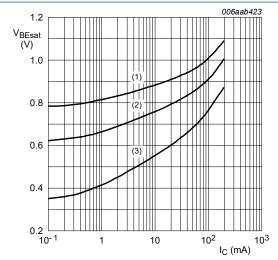
 $V_{CE} = 5 V$

(1) T_{amb} = -55 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



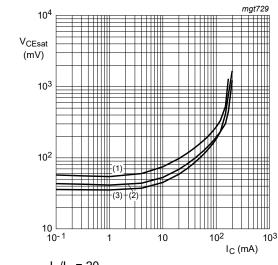
 $I_{\rm C}/I_{\rm B} = 20$

(1) T_{amb} = -55 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

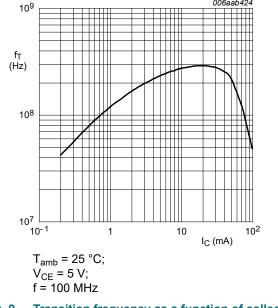


$$I_{\rm C}/I_{\rm B} = 20$$

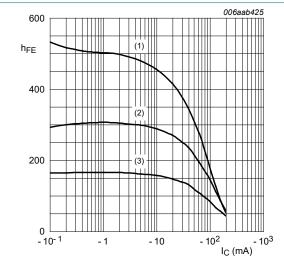
$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 150 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = -55 \,^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



Transition frequency as a function of collector Fig. 9. current; typical values



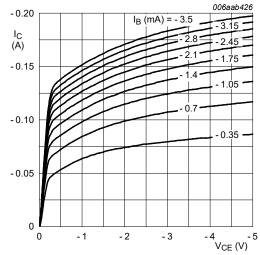
 V_{CE} = -5 V

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values

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45 V, 100 mA NPN/PNP general-purpose transistor

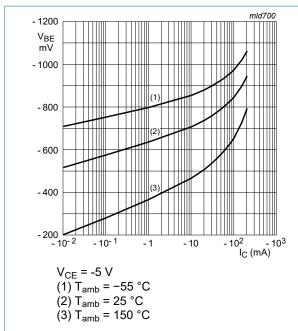


Fig. 12. PNP TR2: Base-emitter voltage as a function of collector current; typical values

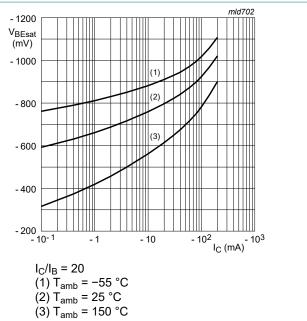


Fig. 13. PNP TR2: Base-emitter saturation voltage as a function of collector current; typical values

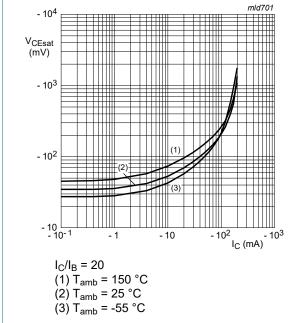
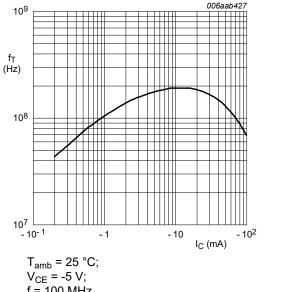


Fig. 14. PNP TR2: Collector-emitter saturation voltage as a function of collector current; typical values



f = 100 MHz

Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values

11. Test information

Quality information

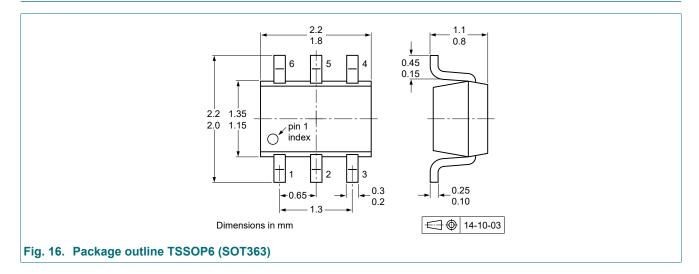
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

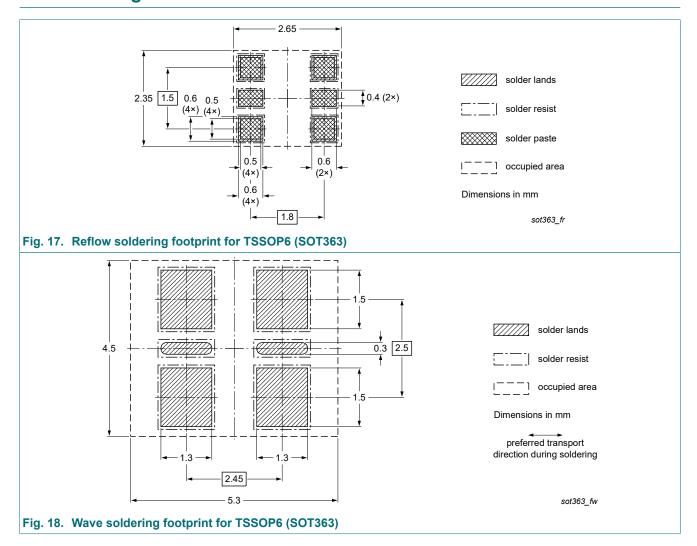


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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847BPN-Q v.1	20210617	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 17 June 2021

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